

TO-92B



ECB

2SA1015 is PNP silicon planar transistor designed for audio frequency general purpose amplifier applications and driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|----------|---------------|
| Collector-Base Voltage | VCBO | 50V |
| Collector-Emitter Voltage | VCEO | 50V |
| Emitter-Base Voltage | VEBO | 5V |
| Collector Current | IC | 150mA |
| Total Power Dissipation | Ptot | 400mW |
| Operating Junction & Storage Temperature | Tj, Tstg | -55 to +125°C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | TEST CONDITIONS |
|--------------------------------------|----------|----------|-----|------|-----------------------------------|
| Collector Cutoff Current | ICBO | | 100 | nA | VCB=50V IE=0 |
| Emitter Cutoff Current | IEBO | | 100 | nA | VEB=5V IC=0 |
| D.C. Current Gain | HFE | 70 25 | 400 | | IC=2mA VCE=6V IC=150mA VCE=6V* |
| Collector-Emitter Saturation Voltage | VCE(sat) | | 0.3 | V | IC=100mA IB=10mA* |
| Base-Emitter Saturation Voltage | VBE(sat) | | 1.1 | V | IC=100mA IB=10mA* |
| Current Gain-Bandwidth Product | fT | 80 | | MHz | IC=1mA VCE=10V |
| Output Capacitance | Cob | | 7 | pF | VCB=10V f=1MHz |
| Noise Figure | NF | | 10 | dB | IC=100µA VCB=6V Rg=10KΩ f=1KHz |

* Pulse Test : Pulse Width = 300µs, Duty Cycle = 2%.

HFE Grouping @ IC=2mA VCE=6V

O : 70-140 Y : 120-240 GR : 200-400

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1-1. Dmp